

2SD468

Silicon NPN Epitaxial

REJ03G0766-0200
 (Previous ADE-208-1135)
 Rev.2.00
 Aug.10.2005

Application

- Low frequency power amplifier
- Complementary pair with 2SB562

Outline

RENESAS Package code: PRSS0003DC-A
 (Package name: TO-92 Mod)



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings

(Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|------------------------------|---------------|-------------|------|
| Collector to base voltage | V_{CBO} | 25 | V |
| Collector to emitter voltage | V_{CEO} | 20 | V |
| Emitter to base voltage | V_{EBO} | 5 | V |
| Collector current | I_C | 1.0 | A |
| Collector peak current | $i_{C(peak)}$ | 1.5 | A |
| Collector power dissipation | P_C | 0.9 | W |
| Junction temperature | T_j | 150 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |

Electrical Characteristics

(Ta = 25°C)

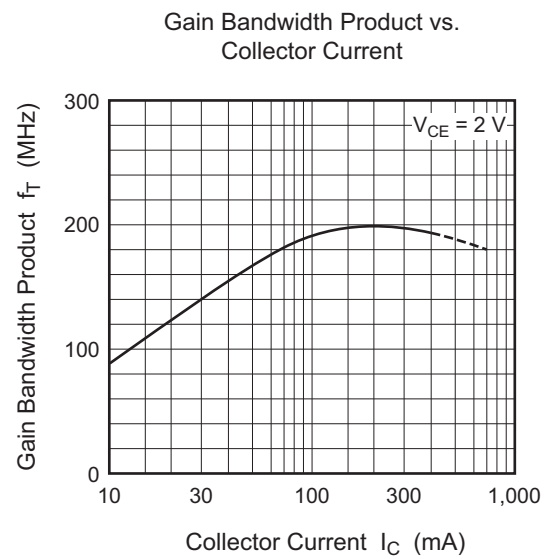
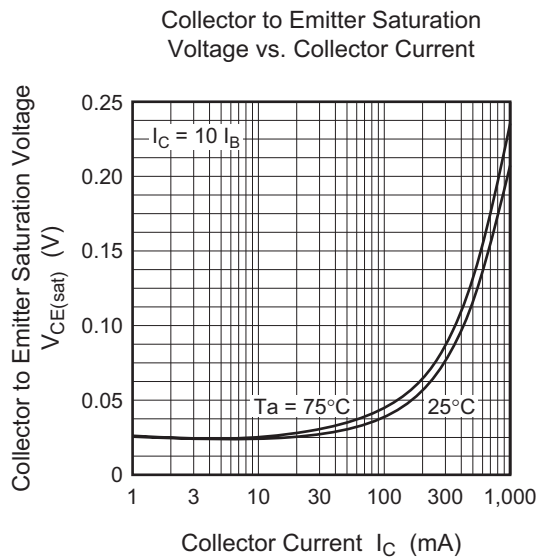
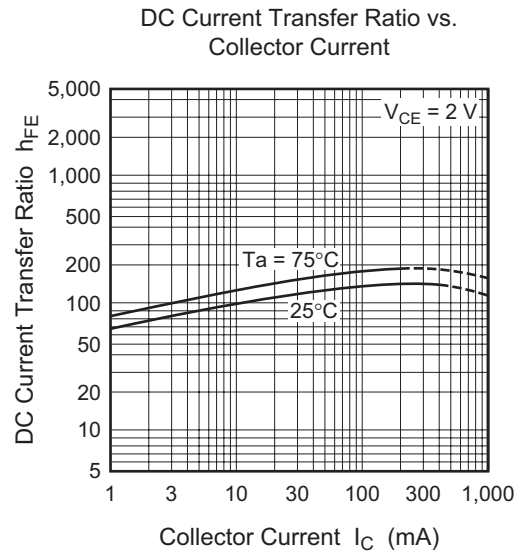
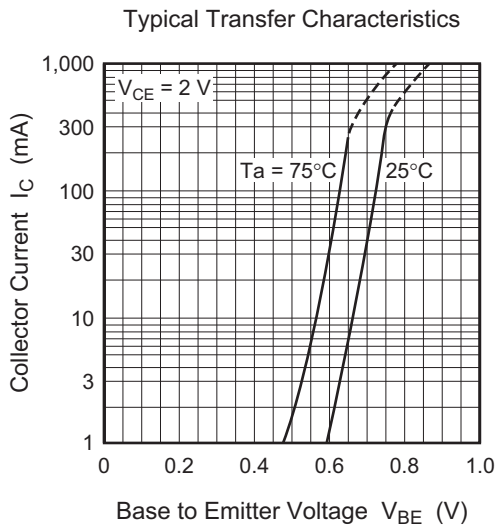
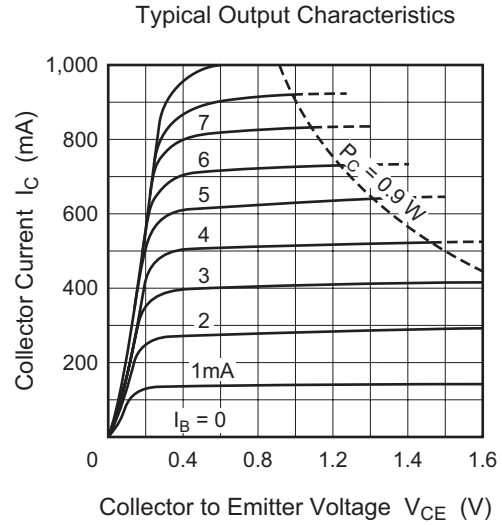
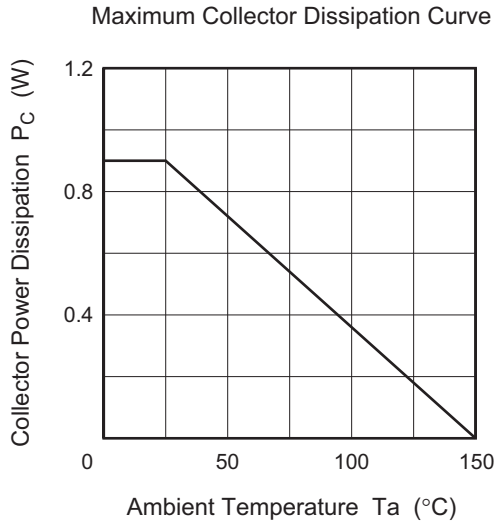
| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|---------------|-----|------|-----|---------|---|
| Collector to base breakdown voltage | $V_{(BR)CBO}$ | 25 | — | — | V | $I_C = 10 \mu A, I_E = 0$ |
| Collector to emitter breakdown voltage | $V_{(BR)CEO}$ | 20 | — | — | V | $I_C = 1 \text{ mA}, R_{BE} = \infty$ |
| Emitter to base breakdown voltage | $V_{(BR)EBO}$ | 5 | — | — | V | $I_E = 10 \mu A, I_C = 0$ |
| Collector cutoff current | I_{CBO} | — | — | 1.0 | μA | $V_{CB} = 20 \text{ V}, I_E = 0$ |
| DC current transfer ratio | h_{FE}^{*1} | 85 | — | 240 | | $V_{CE} = 2 \text{ V}, I_C = 0.5 \text{ A}^{*2}$ |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | — | 0.2 | 0.5 | V | $I_C = 0.8 \text{ A}, I_B = 0.08 \text{ A}^{*2}$ |
| Base to emitter voltage | V_{BE} | — | 0.79 | 1.0 | V | $V_{CE} = 2 \text{ V}, I_C = 0.5 \text{ A}^{*2}$ |
| Gain bandwidth product | f_T | — | 190 | — | MHz | $V_{CE} = 2 \text{ V}, I_C = 0.5 \text{ A}^{*2}$ |
| Collector output capacitance | C_{ob} | — | 22 | — | pF | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ |

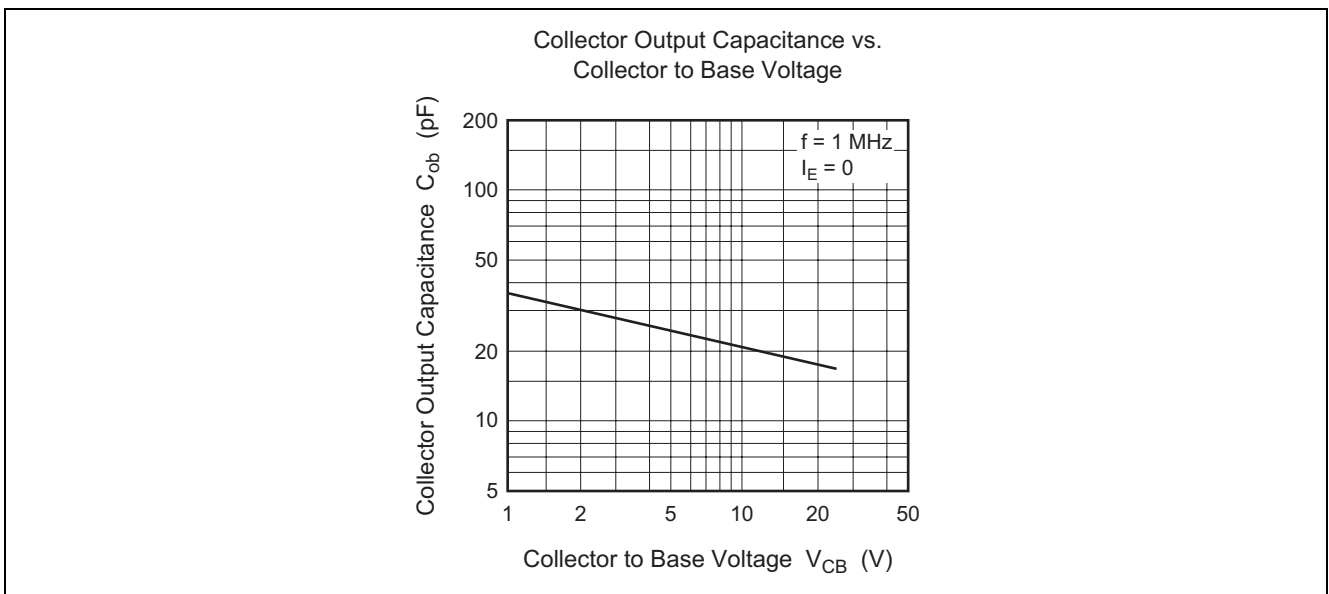
Notes: 1. The 2SD468 is grouped by h_{FE} as follows.

2. Pulse test

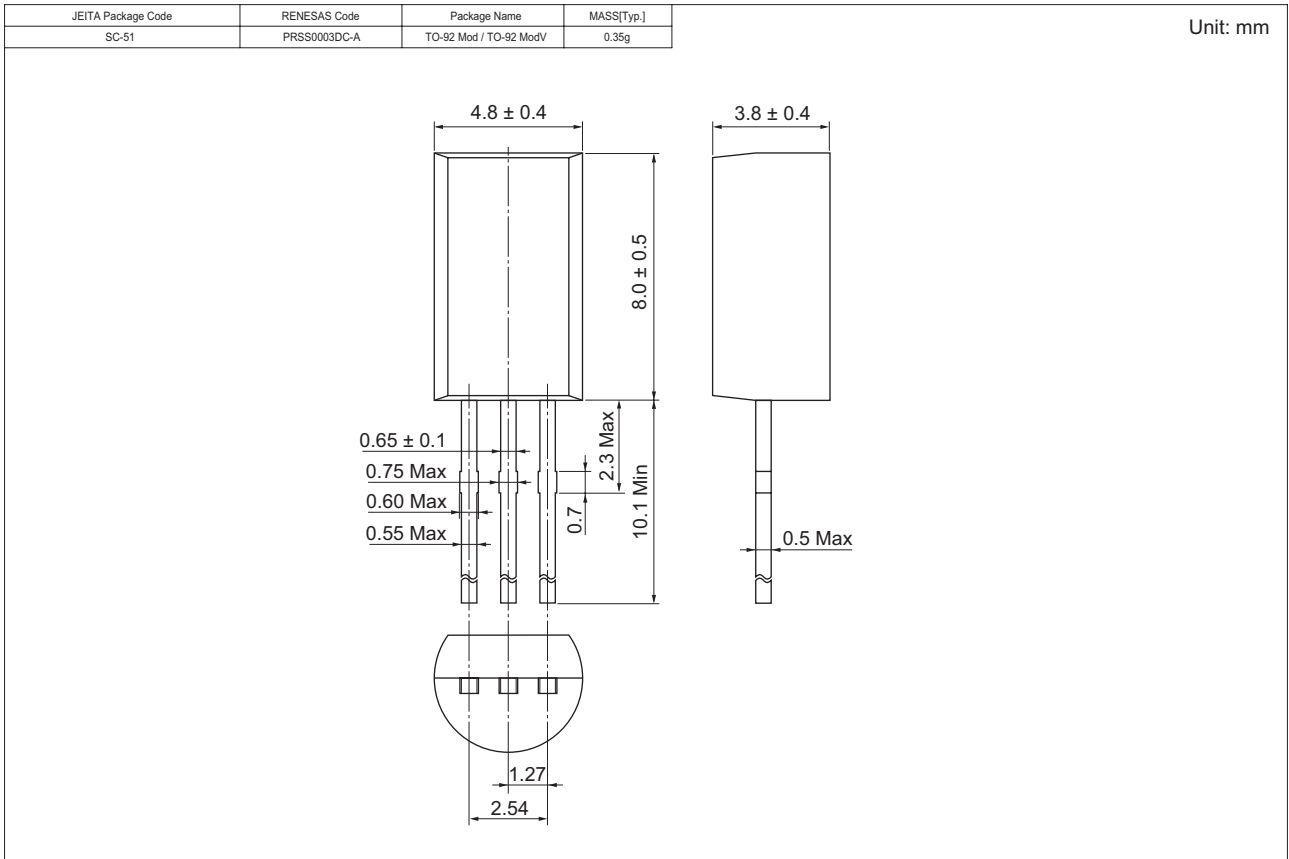
| B | C |
|-----------|------------|
| 85 to 170 | 120 to 240 |

Main Characteristics





Package Dimensions



Ordering Information

| Part Name | Quantity | Shipping Container |
|----------------------------|----------|-------------------------|
| 2SD468BTZ-E 2SD468CTZ-E | 2500 | Hold Box, Radial Taping |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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